

Datasheet

DS-CoreControl-TDA21107

TDA21107

Published by Infineon Technologies AG

<http://www.infineon.com/DCDC>

Power Management & Drive



Never stop thinking.

Contents:

Features.....	3
Application.....	3
Pinout Drawing and Description.....	3
General Description.....	4
Block Diagram.....	4
Application Circuit.....	5
Absolute Maximum Rating	6
Thermal Characteristic.....	7
Operation Condition.....	7
Electrical Characteristic	8
Outline Dimension.....	9
Revision History.....	10
Sales Office Worldwide.....	11

High speed Driver with bootstrapping for dual Power MOSFETs



P-DSO-8

Features:

- Fast rise and fall times for frequencies up to 1 MHz
- Adjustable High Side MOSFET gate drive voltage via external voltage supply to BOOT for optimizing ON losses and gate drive losses (5V to 12V is recommended)
- Prevents from cross-conducting by adaptive gate drive control
- Supports shut-down mode for very low quiescent current through three-state input
- Compatible to standard PWM controller ICs (IFX, Intersil, Analog Devices, Richtek)
- Floating High Side MOSFET drive
- Power-on Overvoltage Protection
- Footprint compatible to ADP3418
- Ideal for multi-phase Desktop CPU supplies on motherboards and VRM's

Application:

- Voltage Regulator Modules
- Low Output Voltage High Output Current DC-DC Converters
- Half-Bridge Class D Amplifier

Type	Package	Marking	Ordering Code
TDA21107	P-DSOP-8	21107	Q67042-S4251

Pinout Drawing and Description:

Number	Name	Description
1	BOOT	Floating bootstrap pin. To be connected to the external bootstrap capacitor to generate the gate drive voltage for the high side N-Channel MOSFET
2	PWM	Input for the PWM signal from controller
3	NC	No Connection
4	VCC	Supply voltage
5	GATE _{LS}	Gate drive output for the N-Channel Low Side MOSFET
6	GND	Ground
7	PHASE	To be connected to the junction of the High Side and the Low Side MOSFET
8	GATE _{HS}	Gate drive output for the N-Channel High side MOSFET

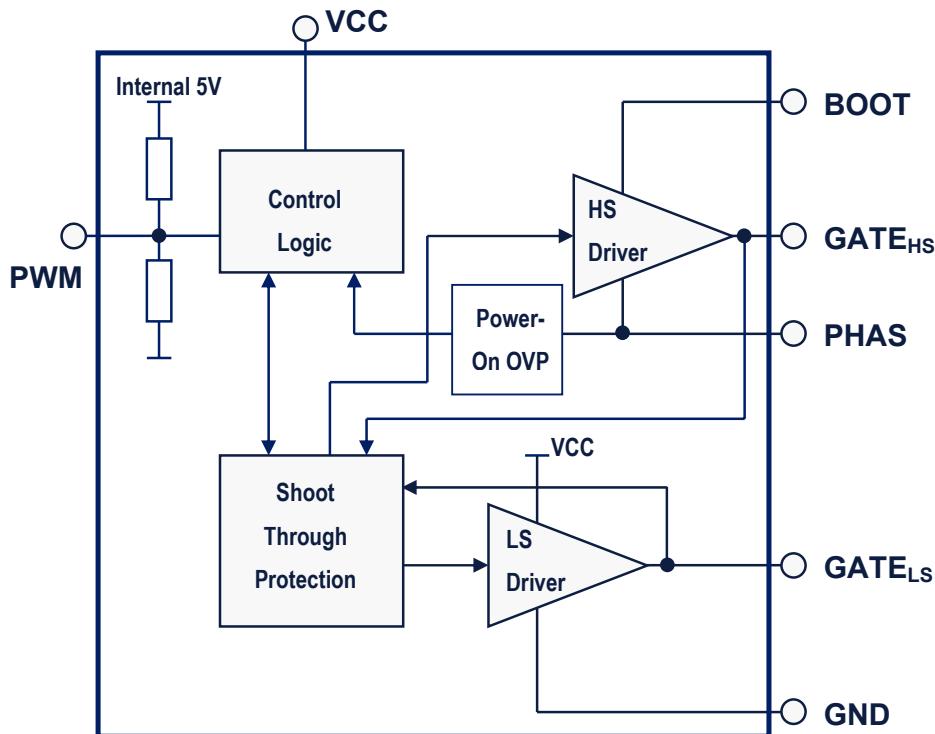
General Description

The dual high speed driver is designed to drive a wide range of N-Channel low side and N-Channel high side MOSFETs with varying gate charges. It has a small propagation delay from PWM input pin to GATE_{HS} and GATE_{LS}, short rise and fall times and the same pin configuration as the ADP3418. In addition it provides several protection features as well as a shut down mode for efficiency reasons.

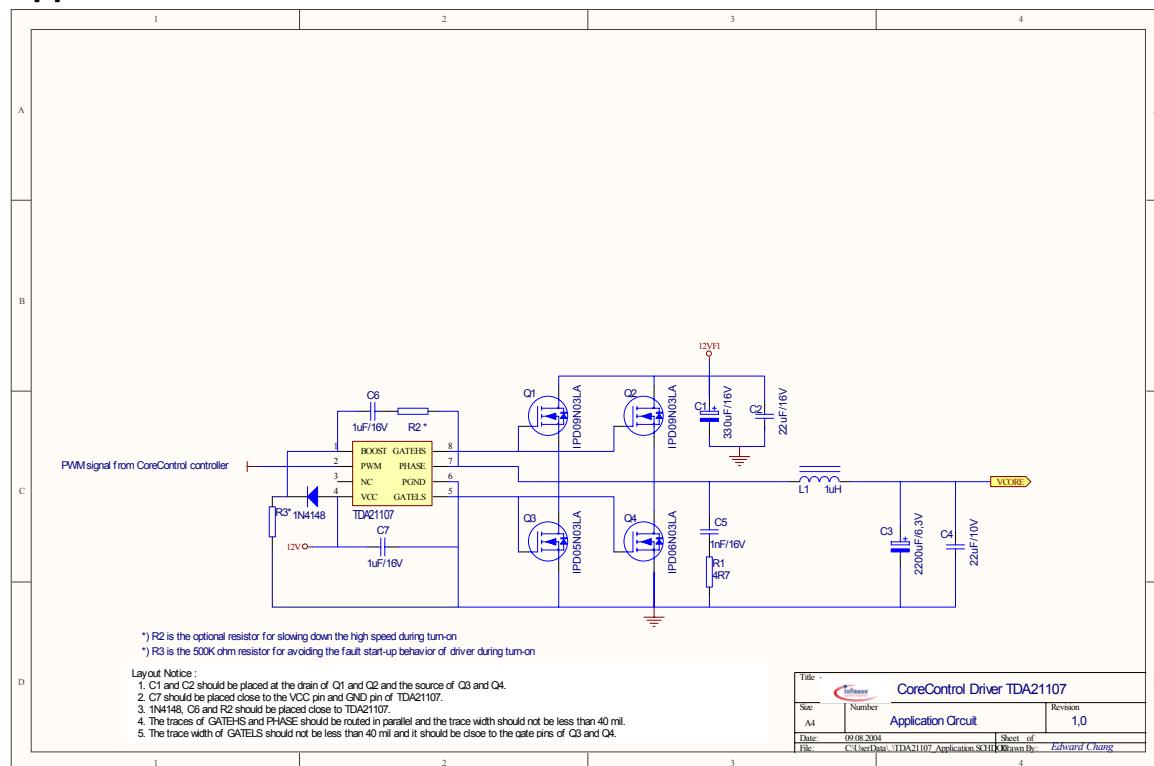
Target application

The dual high speed driver is designed to work well in half-bridge type circuits where dual N-Channel MOSFETs are utilized. A circuit designer can fully take advantage of the driver's capabilities in high-efficiency, high-density synchronous DC/DC converters that operate at high switching frequencies, e.g. in multi-phase converters for CPU supplies on motherboards and VRM's but also in motor drive and half bridge class-D amplifier type applications.

Block Diagram



Application Circuit



Absolute Maximum Ratings

At $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value		Unit
		Min	MAX	
Voltage supplied to 'VCC' pin; DC	V_{VCC}	-0.3	15	V
Voltage supplied to 'PWM' pin	V_{PWM}	-0.3	7	
Voltage supplied to 'BOOT' pin referenced to 'PHASE'	$V_{BOOT} - V_{PHASE}$	-0.3	15	
Voltage supplied to 'BOOT' pin referenced to 'GND'	V_{BOOT}	-0.3	30	
Voltage rating at 'PHASE' pin,	V_{PHASE}	-4	15	
Voltage supplied to GATE_{HS} pin referenced to 'PHASE'	$V_{\text{GATE}_{HS}}$	V_{PHASE}	V_{BOOT}	
		-0.3	+0.3	
Voltage supplied to GATE_{LS} pin referenced to 'GND'	$V_{\text{GATE}_{LS}}$	-0.3	V_{VCC}	
			+0.3	
Junction temperature	T_J	0	150	$^\circ\text{C}$
Storage temperature	T_S	-40	150	
Lead temperature (Soldering, 10 seconds)			260	
ESD Rating; Human Body Model			2	KV
Machine Mode			200	V
IEC climatic category; DIN EN 60068-1	55/150/56			

Thermal Characteristic

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal resistance, junction-soldering point			90		K/W
Thermal resistance, junction-ambient			125		

Operating Conditions

At $T_J = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Voltage supplied to 'VCC' pins	V_{VCC}		10.8	12.0	13.2	V
Input signal transition frequency	f		50		500	KHz
Power dissipation	P_{TOT}	$T_A = 25^\circ\text{C}, T_J = 125^\circ\text{C}$		0.8		W
Junction temperature	T_J		0		125	$^\circ\text{C}$
Ambient temperature	T_A		0		70	$^\circ\text{C}$

Electrical Characteristic

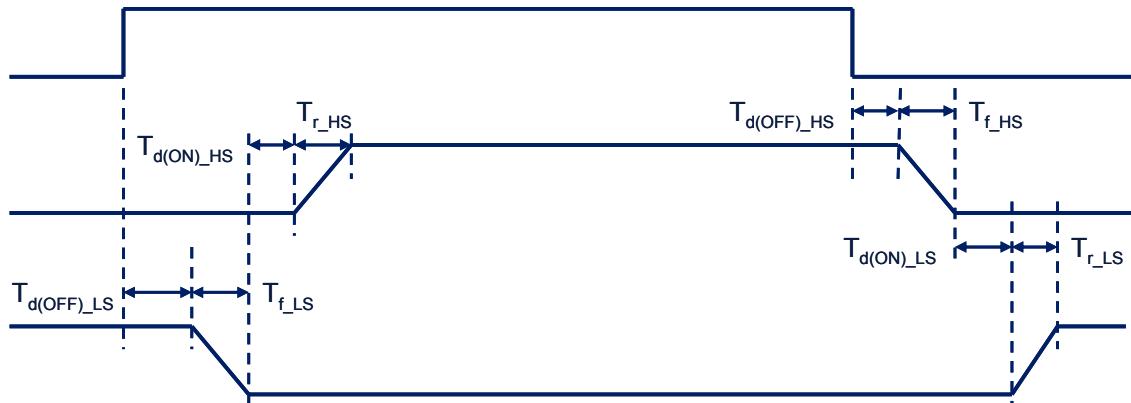
At $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Supply Characteristic						
VCC supply current	I_{VCC}	$V_{VCC} = 12\text{ V}$ $V_{PWM} = 0\text{V}$		5	7	mA
Under-voltage lockout		V_{VCC} rising threshold	8.6	9.4	10.2	V
Under-voltage lockout		V_{VCC} falling threshold	7.25	8.05	8.85	
Input Characteristic						
Current in 'PWM' pin	I_{PWM_L}	$V_{PWM} = 0\text{ V}$	-80	-110	-140	μA
Current in 'PWM' pin	I_{PWM_H}	$V_{PWM} = 5\text{ V}$	80	110	140	
PWM pin open	V_{PWM_O}		2.2	2.5	2.8	V
PWM Low level	V_{PWM_L}		1.2	1.4	1.5	
PWM High level	V_{PWM_H}		3.0	3.5	3.8	

At $T_j = 25^\circ\text{C}$, unless otherwise specified

Dynamic Characteristic					
Turn-on propagation Delay High Side	$t_{d(\text{ON})_HS}$	$P_{PVCC} = V_{VCC} = 12\text{ V}$ $C_{ISS} = 3000\text{ pF}$	40		
Turn-off propagation delay High Side	$t_{d(\text{OFF})_HS}$		30		
Rise time High Side	t_{r_HS}		30		
Fall time High Side	t_{f_HS}		40		
Turn-on propagation Delay Low Side	$t_{d(\text{ON})_LS}$		35		
Turn-off propagation delay Low Side	$t_{d(\text{OFF})_LS}$		30		
Rise time Low Side	t_{r_LS}		30		
Fall time Low Side	t_{f_LS}		30		

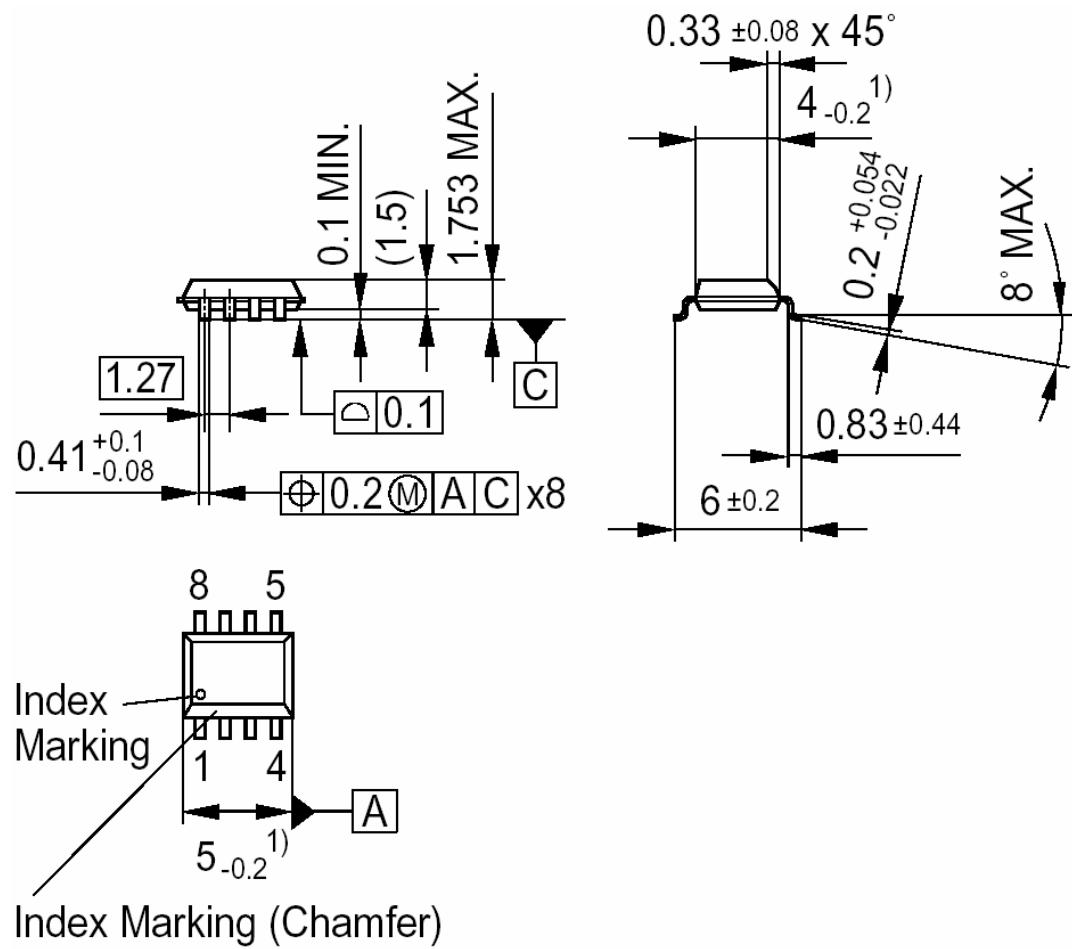
Timing diagram



At $T_j = 25^\circ\text{C}$, unless otherwise specified

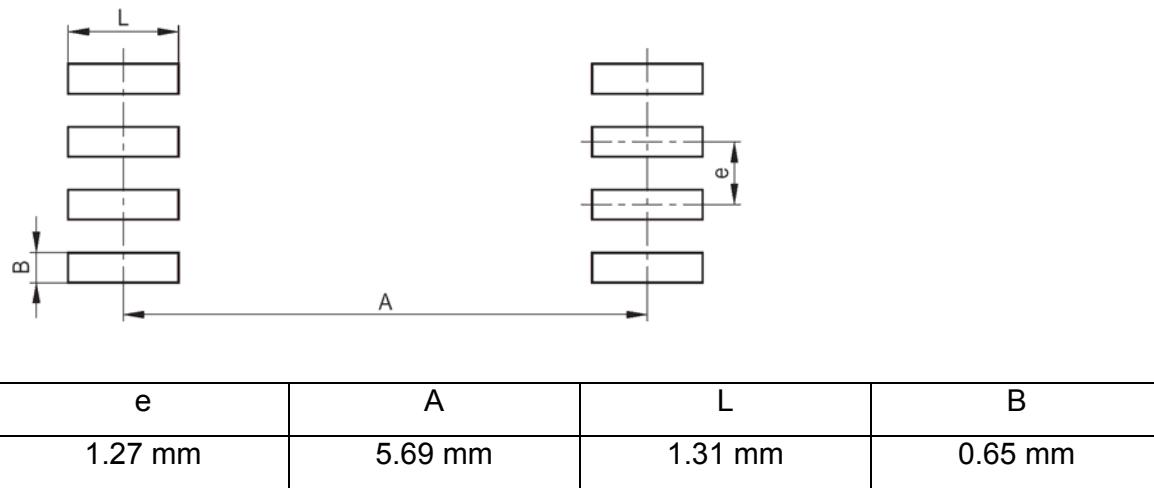
Parameter	Conditions	Values			Unit
		Min.	Typ.	Max.	
Output Characteristic High Side (HS) and Low Side (LS), ensured by design					
Output Resistance	HS; Source	$V_{PVCC} = V_{VCC} = 12\text{ V}$	2		Ω
	HS; Sink		1.5		
	LS; Source		1.6		
	LS; Sink		1.2		

Package Drawing P-DSO-8



¹⁾ Does not include plastic or metal protrusion of 0.15 max. per side

Footprint Drawing P-DSO-8



Revision History

Datasheet DS-CoreControl-TDA21107

Actual Release: V1.1	Date: 22.03.2005	Previous Release: V1.0	Date: 10.08.2004
Page of actual Rel.	Page of prev. Rel.	Subjects changed since last release	
9	9	Add $t_{d(OFF), HS} = 30$ ns and $t_{d(OFF), LS} = 30$ ns	

For questions on technology, delivery and prices please contact the Infineon Technologies Offices in Germany or the Infineon Technologies Companies and Representatives worldwide: see the address list on the last page or our webpage at

<http://www.infineon.com/DCDC>

CoreControl™, **OptiMOS™** and **OptiMOS II™** are trademarks of Infineon Technologies AG.

We listen to Your Comments

Any information within this dokument that you feel is wrong, unclear or missing at all?

Your feedback will help us to continuously improve the quality of this dokument.

Please send your proposal (including a reference to this dokument) to:

mcdoku.comment@infineon.com



Edition 2004-08-10

Published by Infineon Technologies AG,
St.-Martin-Strasse 53,
D-81541 München

© Infineon Technologies AG 2004.
All Rights Reserved.

Attention please!

The information herein is given to describe certain components and shall not be considered as warranted characteristics.

Terms of delivery and rights to technical change reserved.

We hereby disclaim any and all warranties, including but not limited to warranties of non-infringement, regarding circuits, descriptions and charts stated herein.

Infineon Technologies is an approved CECC manufacturer.

Information

For further information on technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies Office in Germany or our Infineon Technologies Representatives worldwide (see address list).

Warnings

Due to technical requirements components may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies Office.

Infineon Technologies Components may only be used in life-support devices or systems with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system, or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body, or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.

INFINEON TECHNOLOGIES AG Sales Offices Worldwide *

Austria Infineon Technologies Austria AG Operngasse 20b/31 A-1040 Wien T (+43) 1-58 7-70 70 0 Fax (+43) 1-58 7-70 70 20	Infineon Technologies AG Paderborner Straße 1 30539 Hannover T (+49) 5 11 87 65 62 0 Fax (+49) 5 11 87 65 62 90	Malaysia Infineon Technologies (M) SDN BHD Krystal Point II 1-4-11/12, Lebuh Bukit Kecil 6 11900 Bayan Lepas Penang, Malaysia T (+60) 46 44 77 66 Fax (+60) 46 41 48 72	USA Infineon Technologies North America Corporation 3700 West Parmer Lane, Suite 102 Austin, TX 78727 T (+1) 51 23 41 71 27 Fax (+1) 51 23 41 99 26
Australia Siemens Ltd. 885 Mountain Highway Bayswater, Victoria 3153 T (+61) 3-97 21 21 11 Fax (+61) 3-97 21 72 75	Infineon Technologies AG Rosenheimer Straße 116 81669 München T (+49) 89 23 40 Fax (+49) 89 23 42 46 94	New Zealand Infineon Technologies AG Südwestpark 65 90449 Nürnberg T (+49) 9 11 -2 52 93 0 Fax (+49) 9 11 -2 52 93 93	Infineon Technologies North America Corporation 8203 Willow Place South, Suite 660 Houston, TX 77070 T (+1) 28 17 74 05 55 Fax (+1) 28 17 74 05 61
Belgium/Netherlands Infineon Technologies Holding B.V. Sales Division Westblaak 32 3012 KM Rotterdam T (+31) 10 -2 17 68 00 Fax (+31) 10 -2 17 68 19	Infineon Technologies AG Südwestpark 65 90449 Nürnberg T (+49) 9 11 -2 52 93 0 Fax (+49) 9 11 -2 52 93 93	Portugal Siemens S.A. OG Componentes Electronicos Rua Irmaos Siemens,1 Alfragide 2720-093 Amadora T (+351) 21-4 17 85 90 Fax (+351) 21-4 17 80 83	Infineon Technologies North America Corporation 485 Route 1 South Iceland, NJ 08830 T (+1) 73 28 55 92 00 Fax (+1) 73 28 55 92
Brazil Infineon Technologies South America Ltda. Avenida Mutinga,3800-Prédio 3 05110-901 São Paulo-SP T (+55) 11-39 08 25 64 Fax (+55) 11-39 08 27 28	Denmark Infineon Technologies Nordic A/S Herlev Hovedgade 201A DK 2730 Herlev T (+45) 44 50 77 00 Fax (+45) 44 50 77 01	Finland Infineon Technologies Nordic OY Linnoutustie 4A P.O. BOX 276 FIN-02601 Espoo T (+3 58) 10 -6 80 84 00 Fax (+3 58) 10 -6 80 84 01	Russia INTECH electronics ul.Smolnaya,24/1203 125 445 Moskva, Russia T (+70) 95 -4 51 97 37 Fax (+70) 95 -4 51 86 08
Canada Infineon Technologies Corporation 340 March Road,Suite 301 Canada, Ontario K2K 2E2 T (+1) 6 13-5 91 38 35 Fax (+1) 6 13-5 91 89 54	France Infineon Technologies France SAS 39 - 47, Bd. Ornano 93527 Saint-Denis CEDEX2 T (+33) 1 48 09 72 00 Fax (+33) 1 48 09 72 90	Singapore Infineon Technologies Asia Pacific Pte. Ltd. 8 Kallang Sector 349282, Singapore T (+65) 68 40 08 88 Fax (+65) 68 40 xx xx	Eupec Inc. 1050 Route 22 Lebanon, NJ 08833 T (+1) 90 8 -2 36 56 21 Fax (+1) 90 8 -2 36 56 20
China Infineon Technologies International Trade (Shanghai) Co., Ltd Beijing Representative Office 12th Floor, Quantum Plaza No.27 Zhichun Road, Haidian District, Beijing 100083, People's Republic of China T (+86) 10 82 35 61 18 Fax (+86) 10 82 35 54 74	India Infineon Technologies India Pvt. Ltd. 10th Floor, Discoverer Building International Technology Park Whitefield Road Bangalore 560 066, India T (+91) 80 8 41 00 17/18 Fax (+91) 80 8 41 00 12	South Africa Siemens Components P.O. Box 3438 Halfway House 1685 Gauteng, South Africa T (+27) 11 6 52 20 00 Fax (+27) 11 6 52 26 73	Infineon Technologies North America Corporation 21800 Haggerty Road, Suite 112 Northville, MI 48167 T (+1) 2 48 -3 74 08 90 Fax (+1) 2 48 -3 74 25 01
Infineon Technologies Hong Kong Ltd, Hong Kong Office 302 Level 3 Festival Walk 80 Tat Chee Avenue, Kowloon Tong Hong Kong T (+852) 28 32 05 00 Fax (+852) 28 27 97 62	Ireland Infineon Technologies Ireland Ltd. 69 Fitzwilliam Lane Dublin 2, Ireland T (+35) 31 79 99 500 Fax (+35) 31 79 99 501	Spain Siemens S.A. Division Components Ronda de Europa, 5 28760 Tres Cantos-Madrid T (+34) 91 5 14 71 54 Fax (+34) 91 5 14 70 13	Infineon Technologies North America Corporation 2901 Dallas N. Tollway, Suite 370 Plano, TX 75093 T (+1) 97 23 78 49 46 Fax (+1) 97 24 03 97 89
Infineon Technologies International Trade (Shanghai) Co., Ltd No.8, Lane 647, Songtao Road Zhangjiang Hi-Tech Park Pudong, Shanghai, China	Israel Nisko Ltd. 2A, Habarzel Street Tel Aviv 69710, Israel T (+9 72)3 -7 65 73 00 Fax (+9 72)3 -7 65 73 33	Sweden Infineon Technologies Nordic AB P.O. Box 46 16493 Kista, Sweden T (+46) 8 7 03 59 00 Fax (+46) 8 7 03 59 01	Infineon Technologies North America Corporation 3000 CentreGreen Way Raleigh, NC 27513 T (+1) 91 96 77 27 00 Fax (+1) 91 96 78 19 34
Infineon Technologies International Trade (Shanghai) Co., Ltd Shenzhen Office Room 1501-05, Block A Tian An International Building Renmin Nan Road Shenzhen 518001, China T (+86) 7 55 -2 28 91 04 Fax (+86) 7 55 -2 28 02 17	Italy Infineon Technologies Italy S.r.l. Via Vipiteno 4 20128 Milano, Italy T (+39) 022 52 04 1 Fax (+39) 022 52 04 43 95	Switzerland Infineon Technologies Switzerland AG Badenerstraße 623 P.O. Box 1570 8048 Zürich T (+41) 1 49 78 00 40 Fax (+41) 1 49 78 00 50	Infineon Technologies North America Corporation 6170 Cornerstone Ct East, Suite 240 San Diego, CA 92121 T (+1) 85 85 26 22 01 Fax (+1) 85 85 26 22 02
Germany Infineon Technologies AG Siemensstraße 31-33 71254 Ditzingen/Stuttgart T (+49) 71 56 -1 79 19 10 Fax (+49) 71 56 -1 79 19 90	Japan Infineon Technologies Japan K.K. Takanawa Park Tower 8F/9F/12F/17F 3-20-14, Higashi-Gotanda Shinagawa-ku Tokyo 141-0022, Japan T (+81) 3 54 49 64 11 Fax (+81) 3 54 49 64 01	Taiwan Infineon Technologies Taiwan,Ltd. 12F-1, No.3-2 Yuan Qu. St., Nan Kang Software Park, Taipei Taiwan 115, ROC T (+8 86)2-2655 7500 Fax (+8 86)2-2655 7501-8	Infineon Technologies North America Corporation 1730 North First Street San Jose, CA 95112 T (+1) 408 -5 01 60 00 Fax (+1) 408 -5 01 24 24
Infineon Technologies AG Völklinger Straße 4 40219 Düsseldorf T (+49) 2 11 -20 95 49 0 Fax (+49) 2 11 -20 95 49 60	Korea Infineon Technologies Korea Co., Ltd.. Room No. 2&3,9th floor Daelim Acotel Building 467-6 Dokock-Dong, Kangnam-Gu Seoul, Korea 135-971 T (+82) 23 46 00 900 Fax (+82) 23 46 00 901/902	Turkey Siemens Sanayi ve Ticaret A.S. Yakacik Yolu No.111 34861 Kartal, İstanbul T (+90) 21 64 59 28 51 Fax (+90) 21 64 19 31 90	Infineon Technologies North America Corporation 238 Littleton Road, Suite 200 Westford, MA 01886 T (+1) 97 86 92 05 50 Fax (+1) 97 86 92 23 0
Infineon Technologies AG Naegelsbachstraße 26 91052 Erlangen T (+49) 91 31 97 00 10 Fax (+49) 91 31 97 00 99		United Kingdom Infineon Technologies UK.Ltd. Infineon House Fleet Mill Minley Road Fleet, Hampshire GU51 2RD T (+44) 12 52 77 22 00 Fax (+44) 12 52 77 22 01	* and representative offices